

7MBP150RA120

IGBT-IPM R series

1200V / 150A 7 in one-package

Features

- Temperature protection provided by directly detecting the junction temperature of the IGBTs
- Low power loss and soft switching
- High performance and high reliability IGBT with overheating protection
- Higher reliability because of a big decrease in number of parts in built-in control circuit

Maximum ratings and characteristics

- Absolute maximum ratings(at $T_c=25^{\circ}\text{C}$ unless otherwise specified)

Item			Symbol	Rating		Unit
				Min.	Max.	
DC bus voltage			V_{DC}	0	900	V
DC bus voltage (surge)			$V_{DC}(\text{surge})$	0	1000	V
DC bus voltage (short operating)			V_{SC}	200	800	V
Collector-Emitter voltage			V_{CES}	0	1200	V
DB Reverse voltage			V_R	-	1200	V
INV	Collector current	DC	I_c	-	150	A
		1ms	I_{CP}	-	300	A
		DC	$-I_c$	-	150	A
	Collector power dissipation	One transistor	P_C	-	1040	W
DB	Collector current	DC	I_c	-	50	A
		1ms	I_{CP}	-	100	A
	Forward current of Diode		I_F	-	50	A
	Collector power dissipation	One transistor	P_C	-	400	W
Junction temperature			T_j	-	150	$^{\circ}\text{C}$
Input voltage of power supply for Pre-Driver			V_{CC}^{*1}	0	20	V
Input signal voltage			V_{in}^{*2}	0	V_Z	V
Input signal current			I_{in}	-	1	mA
Alarm signal voltage			V_{ALM}^{*3}	0	V_{CC}	V
Alarm signal current			I_{ALM}^{*4}	-	15	mA
Storage temperature			T_{stg}	-40	125	$^{\circ}\text{C}$
Operating case temperature			T_{op}	-20	100	$^{\circ}\text{C}$
Isolating voltage (Case-Terminal)			V_{iso}^{*5}	-	AC2.5	kV
Screw torque	Mounting (M5)			-	3.5 *6	N·m
	Terminal (M5)			-	3.5 *6	N·m

*1 Apply V_{CC} between terminal No. 3 and 1, 6 and 4, 9 and 7, 11 and 10.

*2 Apply V_{in} between terminal No. 2 and 1, 5 and 4, 8 and 7, 12,13,14,15 and 10.

*3 Apply V_{ALM} between terminal No. 16 and 10.

*4 Apply I_{ALM} to terminal No. 16.

*5 50Hz/60Hz sine wave 1 minute.

*6 Recommendable Value : 2.5 to 3.0 N·m

- Electrical characteristics of power circuit (at $T_c=T_j=25^{\circ}\text{C}$, $V_{CC}=15\text{V}$)

Item		Symbol	Condition	Min.	Typ.	Max.	Unit
INV	Collector current at off signal input	I_{CES}	$V_{CE}=1200\text{V}$ input terminal open	—	—	1.0	mA
	Collector-Emitter saturation voltage	$V_{CE(sat)}$	$I_c=150\text{A}$	—	—	2.6	V
	Forward voltage of FWD	V_F	$-I_c=150\text{A}$	—	—	3.0	V
DB	Collector current at off signal input	I_{CES}	$V_{CE}=1200\text{V}$ input terminal open	—	—	1.0	mA
	Collector-Emitter saturation voltage	$V_{CE(sat)}$	$I_c=50\text{A}$	—	—	2.6	V
	Forward voltage of Diode	V_F	$-I_c=50\text{A}$	—	—	3.3	V

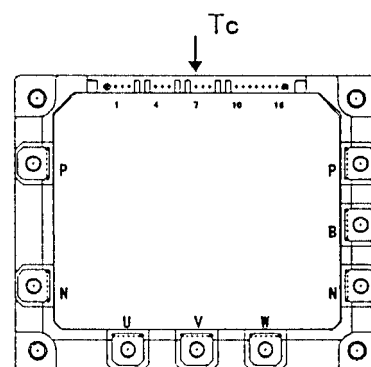
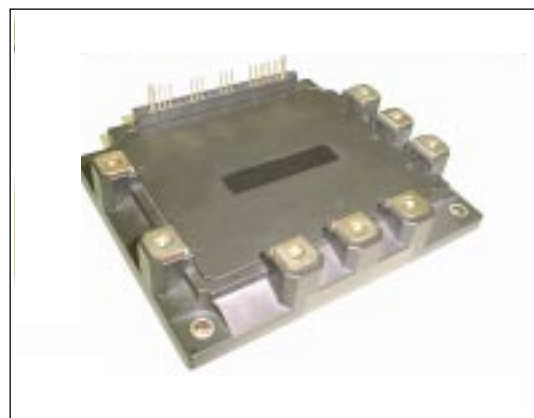


Fig.1 Measurement of case temperature

● **Electrical characteristics of control circuit**(at $T_c=T_j=25^\circ\text{C}$, $V_{cc}=15\text{V}$)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Power supply current of P-line side Pre-driver(one unit)	I_{ccp}	$f_{sw}=0$ to 15kHz $T_c=-20$ to 100°C *7	3	-	18	mA
Power supply current of N-line side three Pre-driver	I_{ccN}	$f_{sw}=0$ to 15kHz $T_c=-20$ to 100°C *7	10	-	65	mA
Input signal threshold voltage (on/off)	$V_{in(th)}$	ON	1.00	1.35	1.70	V
		OFF	1.70	2.05	2.40	V
Input zener voltage	V_z	$R_{in}=20\text{k ohm}$	-	8.0	-	V
Over heating protection temperature level	T_{COH}	$V_{DC}=0\text{V}$, $I_c=0\text{A}$, Case temperature, Fig.1	110	-	125	$^\circ\text{C}$
Hysteresis	T_{CH}		-	20	-	$^\circ\text{C}$
IGBT chips over heating protection temperature level	T_{JOH}	surface of IGBT chips	150	-	-	$^\circ\text{C}$
Hysteresis	T_{JH}		-	20	-	$^\circ\text{C}$
Collector current protection level	INV	I_{oc} $T_j=125^\circ\text{C}$	225	-	-	A
	DB	I_{oc} $T_j=125^\circ\text{C}$	75	-	-	A
Over current protection delay time (Fig.2)	t_{DOC}	$T_j=25^\circ\text{C}$ Fig.2	-	10	-	μs
Under voltage protection level	V_{UV}		11.0	-	12.5	V
Hysteresis	V_H		0.2	-	-	V
Alarm signal hold time	t_{ALM}		1.5	2	-	ms
SC protection delay time	t_{SC}	$T_j=25^\circ\text{C}$ Fig.3	-	-	12	μs
Limiting resistor for alarm	R_{ALM}		1425	1500	1575	ohm

*7 Switching frequency of IPM

● **Dynamic characteristics**(at $T_c=T_j=125^\circ\text{C}$, $V_{cc}=15\text{V}$)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Switching time (IGBT)	t_{on}	$I_C=150\text{A}$, $V_{DC}=600\text{V}$	0.3	-	-	μs
	t_{off}		-	-	3.6	μs
Switching time (FWD)	t_{rr}	$I_F=150\text{A}$, $V_{DC}=600\text{V}$	-	-	0.4	μs

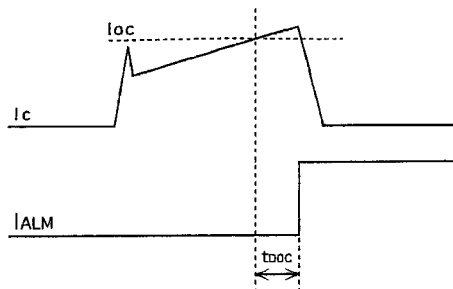


Fig.2 Definition of OC delay time

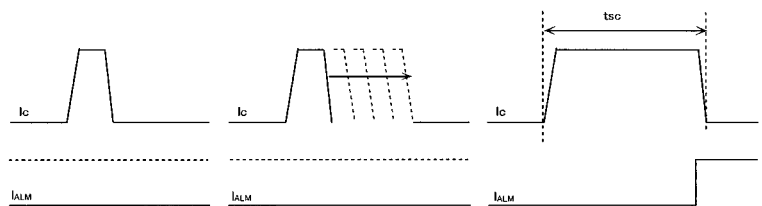


Fig.3 Definition of t_{sc}

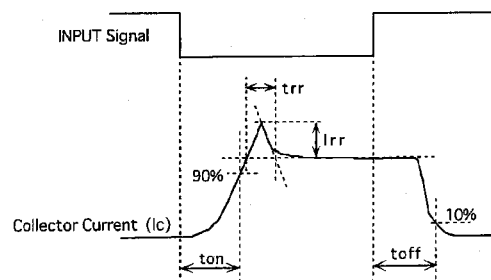


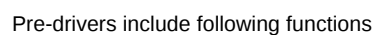
Fig.4 Definition of switching time

● **Thermal characteristics**($T_c=25^\circ\text{C}$)

Item			Symbol	Typ.	Max.	Unit
Junction to Case thermal resistance	INV	IGBT	Rth(j-c)	-	0.12	°C/W
		FWD	Rth(j-c)	-	0.29	°C/W
	DB	IGBT	Rth(j-c)	-	0.31	°C/W
Case to fin thermal resistance with compound			Rth(c-f)	0.05	-	°C/W

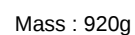
● **Recommendable value**

Item	Symbol	Min.	Typ.	Max.	Unit
DC bus voltage	V_{DC}	200	-	800	V
Operating power supply voltage range of Pre-driver	V_{CC}	13.5	15	16.5	V
Switching frequency of IPM	f_{sw}	1	-	20	kHz
Screw torque	Mounting (M5)	-	2.5	-	N·m
	Terminal (M5)	-	2.5	-	N·m



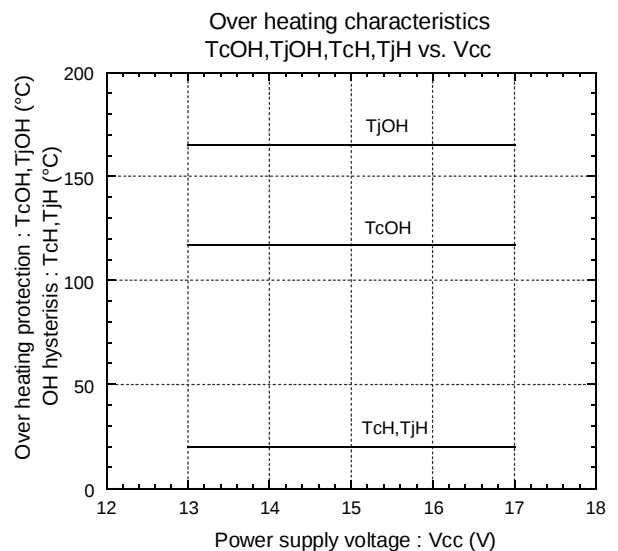
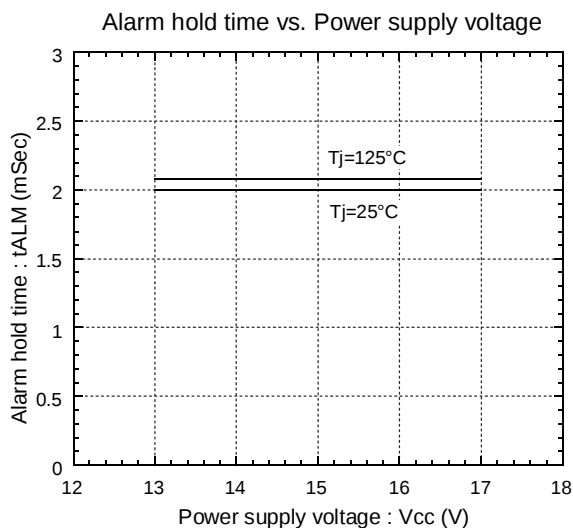
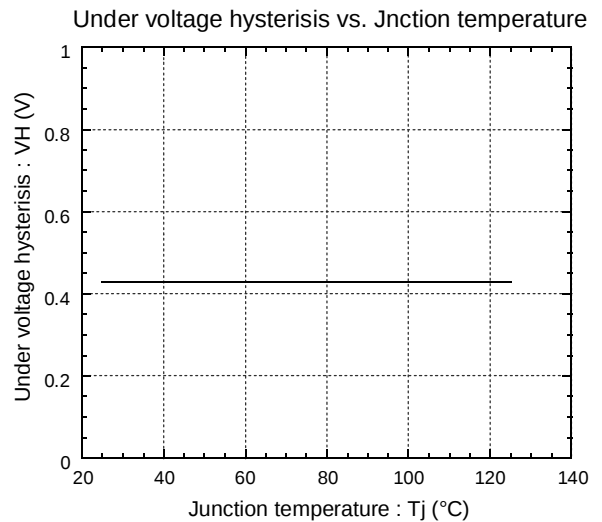
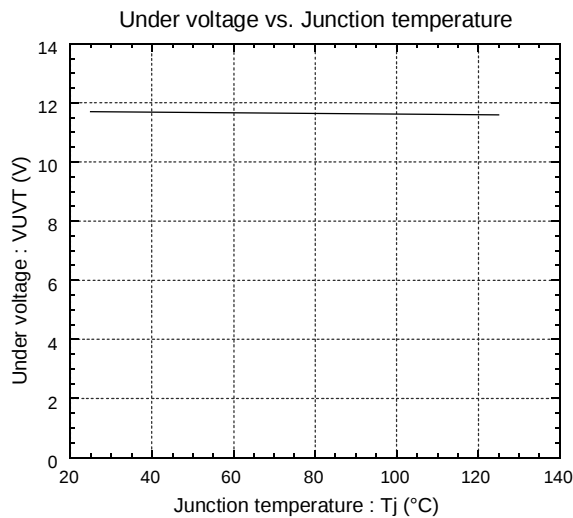
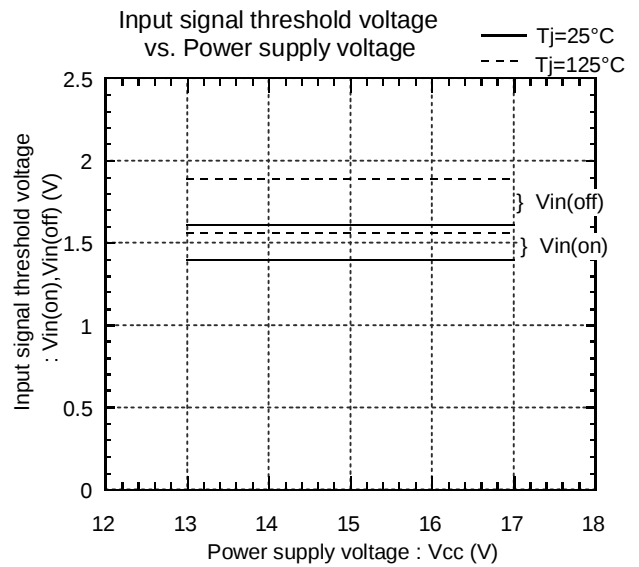
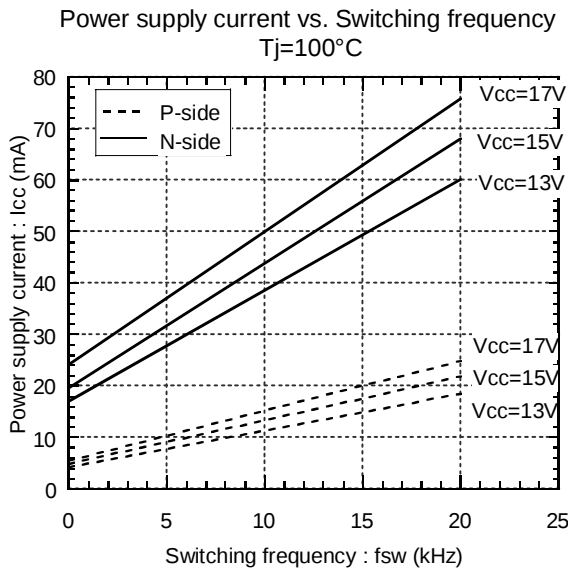
- a) Amplifier for driver
- b) Short circuit protection
- c) Undervoltage lockout circuit
- d) Over current protection
- e) IGBT chip over heating protection

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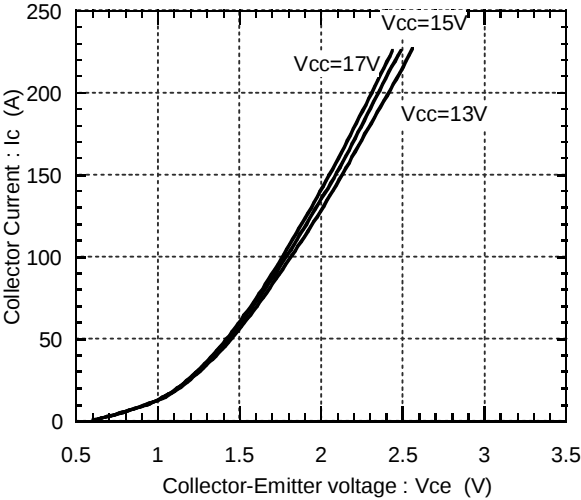
Characteristics (Representative)

Control Circuit

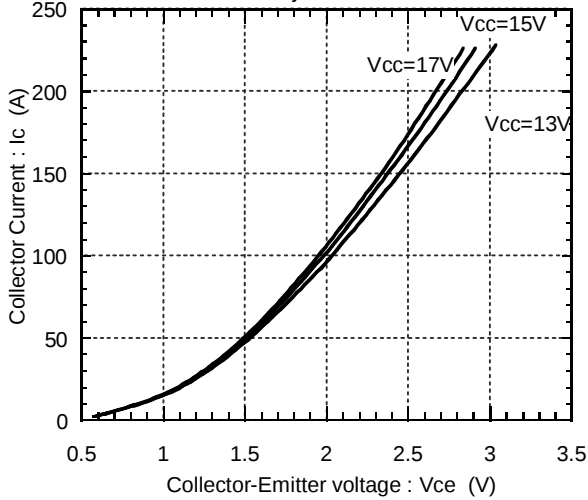


● Inverter

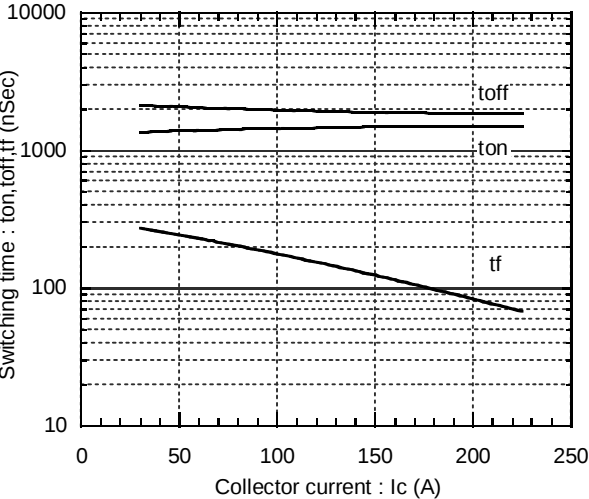
Collector current vs. Collector-Emitter voltage
 $T_j=25^{\circ}\text{C}$



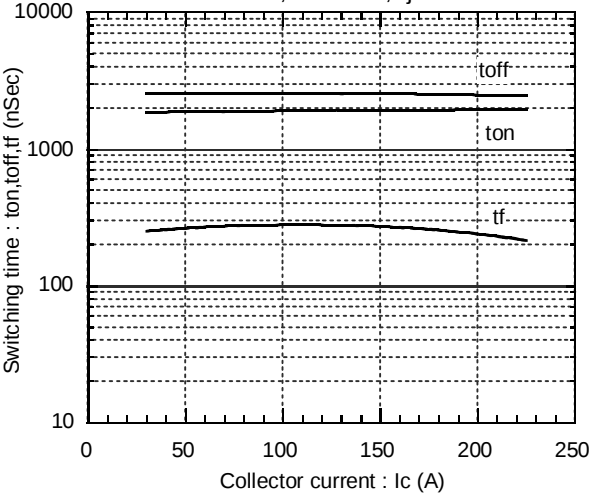
Collector current vs. Collector-Emitter voltage
 $T_j=125^{\circ}\text{C}$



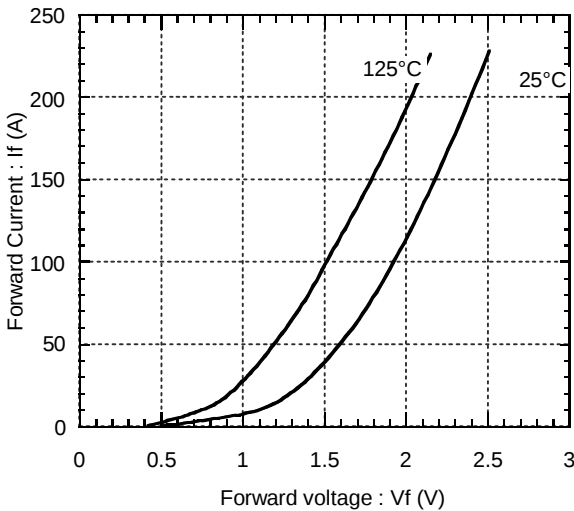
Switching time vs. Collector current
 $E_{dc}=600\text{V}, V_{cc}=15\text{V}, T_j=25^{\circ}\text{C}$



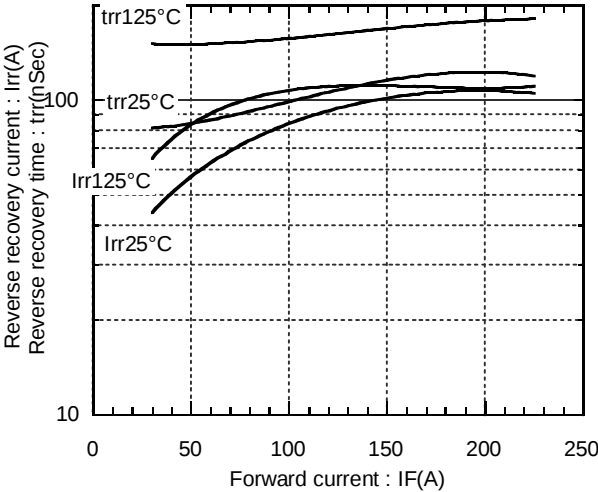
Switching time vs. Collector current
 $E_{dc}=600\text{V}, V_{cc}=15\text{V}, T_j=125^{\circ}\text{C}$

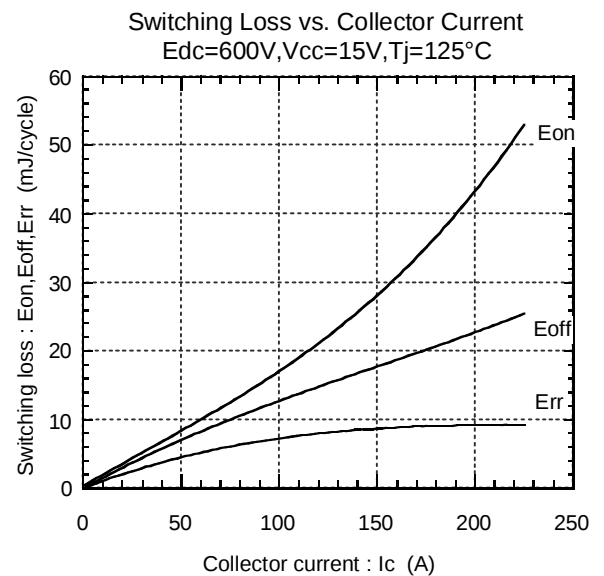
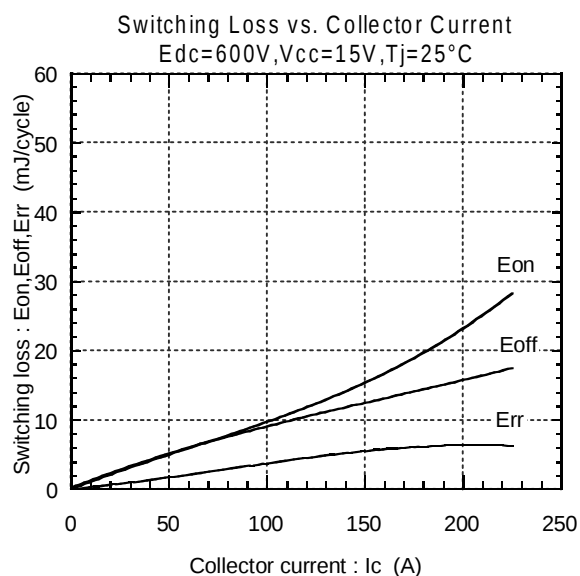
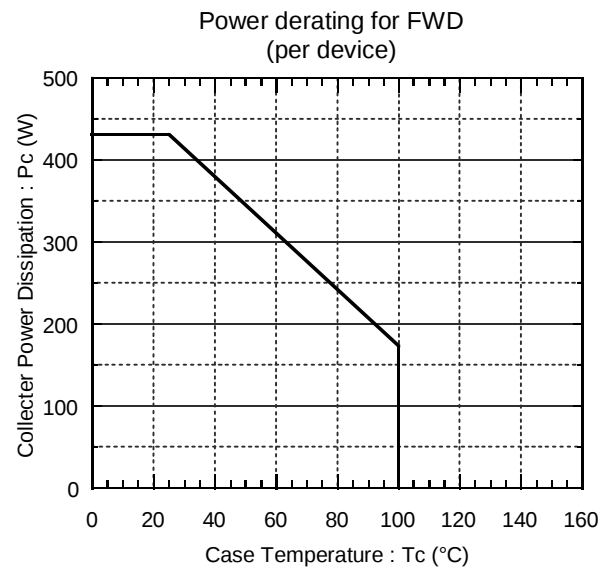
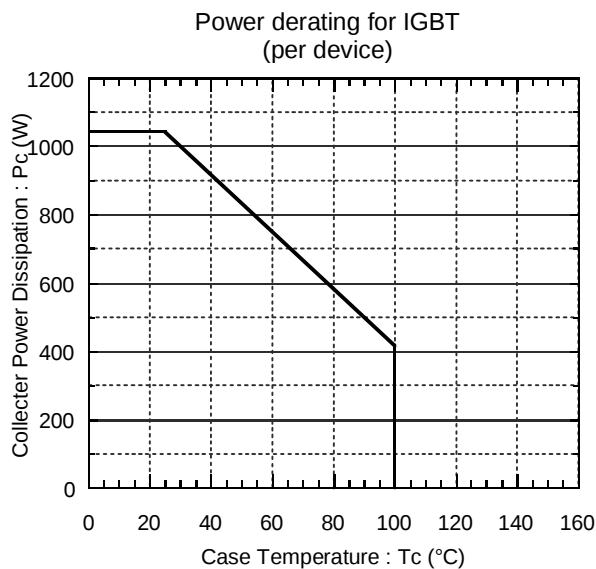
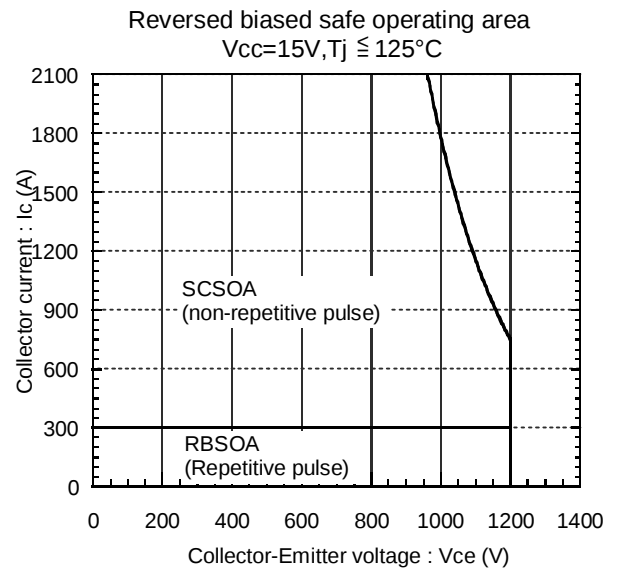
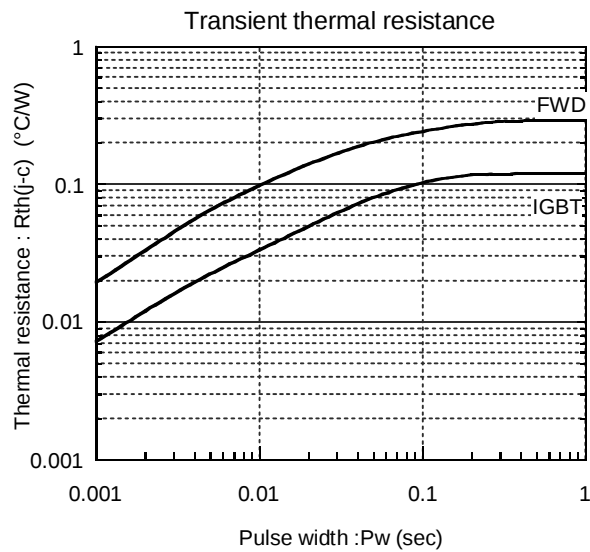


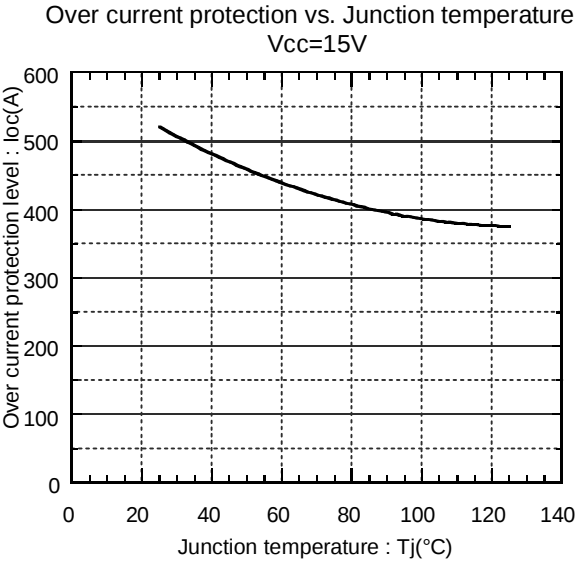
Forward current vs. Forward voltage



Reverse recovery characteristics
 t_{rr}, I_{rr} vs. I_F







● Brake

